

FIG. 1

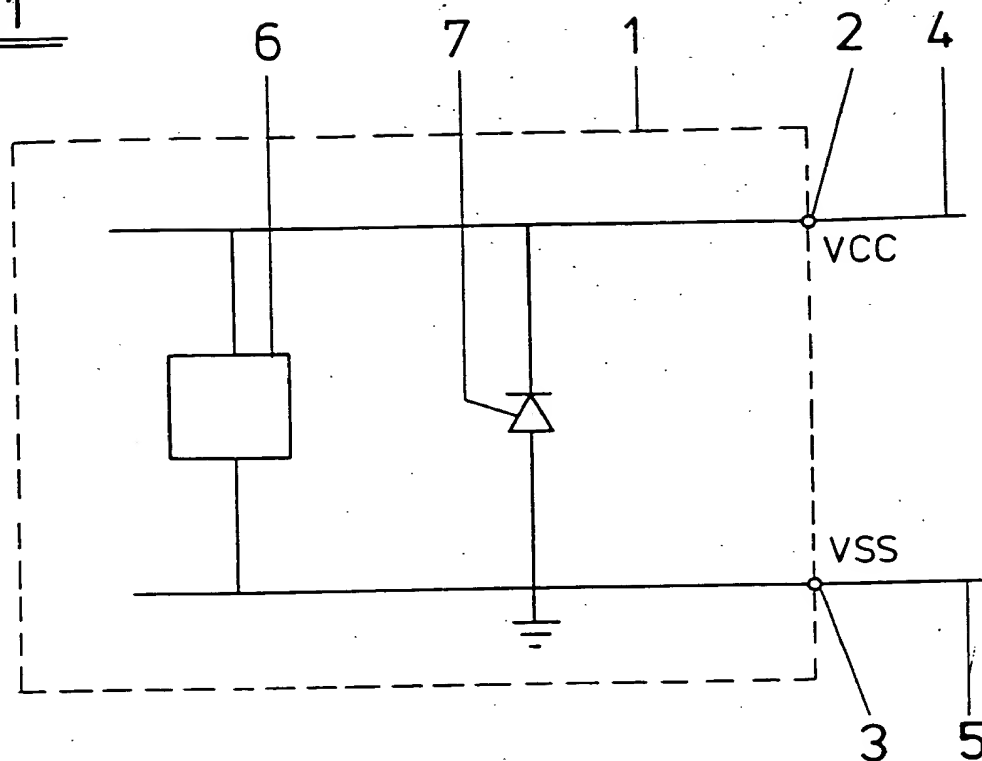
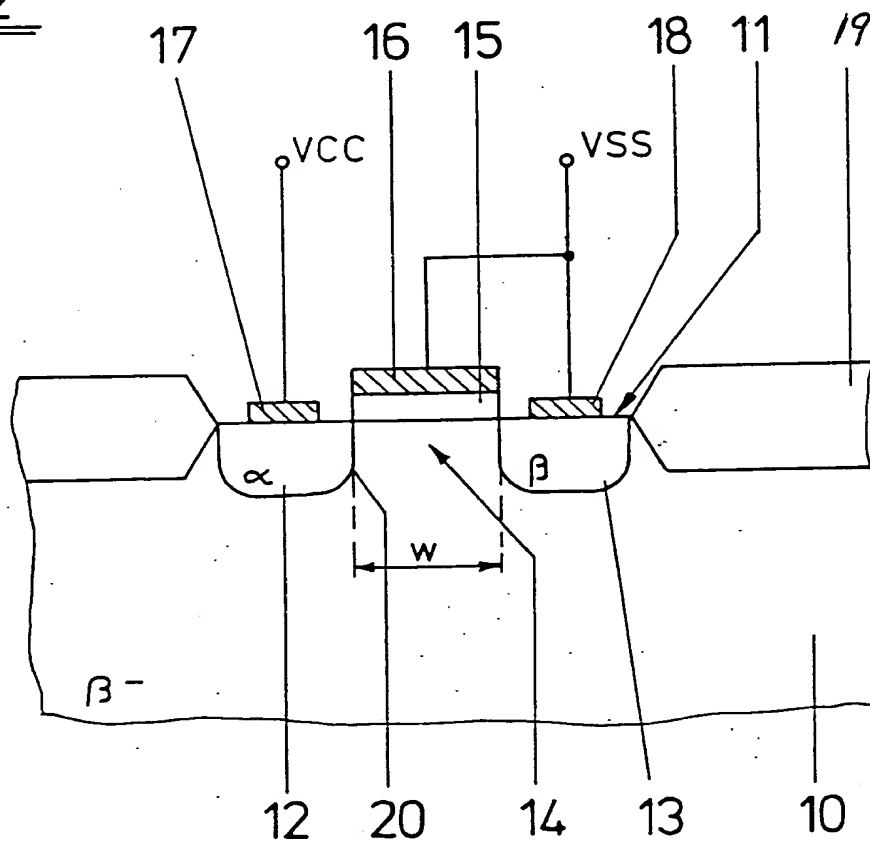


FIG. 2



A cross-sectional diagram of a semiconductor device, likely a multi-gate transistor or a similar structure. The diagram shows a substrate labeled β^- at the bottom. On top of the substrate, there are several regions labeled with Greek letters: β on the left and right, and α in the center. Above these regions are gates, some of which are labeled with numbers 15, 16, and 17. The gates are connected to a common line labeled V_{SS} and V_{CC} . There are also contacts labeled 18, 11, and 19. The diagram is annotated with various numbers (10, 11, 12, 13, 14, 15, 16, 17, 18, 19) and Greek letters (β , α , β^-) indicating different layers and regions. Arrows point to specific features, and a legend at the bottom identifies some of the labels.